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Docket Number (Optional)

SETI-0009

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

"Molecular Beam Epitaxy of Nitride Thin Films," M. J. Paisley et al., Journal of Crystal Growth, Vol. 127, February 2, 1993, pp. 136-142.

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"Strain Energy Bank Engineering Approach to AlN/GaN/InN Heterojunction Devices," A. Khan et al., Frontiers in Electronics: Future Chips Proceedings of the 2002 Workshop on Frontiers in Electronics (WOFE-02) St. Croix, Virgin Islands, World Scientific Publishing Co. (January 15, 2003), pp. 195-214 (1-19).

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